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FDC2512

150V N-Channel PowerTrench® MOSFET

General Description

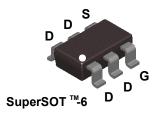
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{\text{DS(ON)}}$ and fast switching speed.

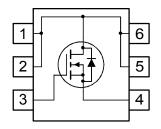
Applications

• DC/DC converter

Features

- 1.4 A, 150 V. $R_{DS(ON)} = 425 \text{ m}\Omega$ @ $V_{GS} = 10 \text{ V}$ $R_{DS(ON)} = 475 \text{ m}\Omega$ @ $V_{GS} = 6 \text{ V}$
- High performance trench technology for extremely low R_{DS(ON)}
- Low gate charge (8nC typ)
- High power and current handling capability
- Fast switching speed





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		150	V
V _{GSS}	Gate-Source Voltage		± 20	V
I _D	Drain Current - Continuous	(Note 1a)	1.4	^
	Pulsed		8	A
E _{AS}	Single Pulse Avalanche Energy	(Note 3)	13.5	mJ
P _D	Maximum Power Dissipation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T _J , T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W	
R _{eJC}	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.252	FDC2512	7"	8mm	3000 units

	ical Characteristics	T _A = 25°C unless otherwise noted	1			
Symbl	Parameter	Test Conditions	Min	Тур	Max	Units
Off Cha	racteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = 250 \mu\text{A}$	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		147		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
I_{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Cha	racteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	2	2.6	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		-5.6		mV/°C
R _{DS(on)}	Static Drain–Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 1.4 \text{ A}$ $V_{GS} = 6.0 \text{ V}, I_D = 1.3 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 1.4 \text{ A}, T_J = 125^{\circ}\text{C}$		319 332 624	425 475 875	mΩ
I _{D(on)}	On–State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	4			Α
g FS	Forward Transconductance	$V_{DS} = 10 \text{ V}, \qquad I_{D} = 1.4 \text{ A}$		4		S
Dynam	ic Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 75 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		344		pF
Coss	Output Capacitance	f = 1.0 MHz		22		pF
C _{rss}	Reverse Transfer Capacitance			9		pF
Switchi	ing Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 75 V, I _D = 1 A,		6.5	13	ns
t _r	Turn-On Rise Time	V_{GS} = 10 V, R_{GEN} = 6 Ω		3.5	7	ns
t _{d(off)}	Turn-Off Delay Time			22	33	ns
t _f	Turn-Off Fall Time			4	8	ns
Q _g	Total Gate Charge	V _{DS} = 75 V, I _D = 1.4 A,		8	11	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		1.5		nC
Q _{gd}	Gate-Drain Charge			2.3		nC
Drain-S	Source Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source	9			1.3	Α
V_{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 1.3 A (Note 2)		0.8	1.2	V
rr	Diode Reverse Recovery Time	$I_F = 1.4A,$		45.8		nS
2 _{rr}	Diode Reverse Recovery Charge	$d_{iF}/d_t = 300 \text{ A/}\mu\text{s}$ (Note 2)		119		nC

Notes:

1.R_{0,1A} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



78°C/W when mounted on a 1in² pad of 2 oz copper



156°C/W when mounted on a minimum pad of 2 oz copper

Scale 1: 1 on letter size paper

- **2.** Pulse Test: Pulse Width < 300μ s, Duty Cycle < 2.0%
- 3. Starting T_J = 25°C; N-ch: L = 3mH, I_{AS} = 3A, V_{DD} = 150V, V_{GS} = 10V; 100% UIL tested.

Typical Characteristics

2.2

Rosioni) NORMALIZED
DRAIN-SOURCE ON-RESISTANCE
9.0
1 8.1

0.2

-50

-25

0

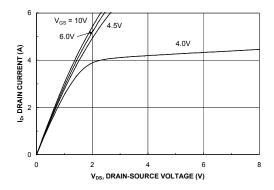


Figure 1. On-Region Characteristics.



150

125

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

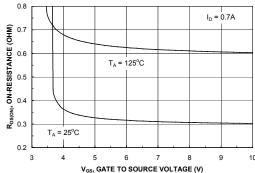


Figure 3. On-Resistance Variation with Temperature.

50

T_J, JUNCTION TEMPERATURE (°C)

75

100

25

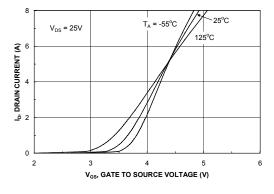


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

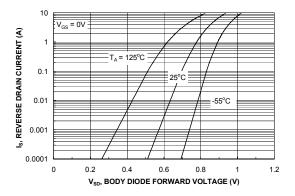
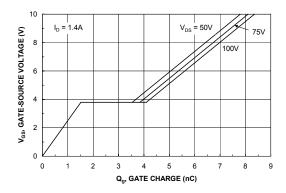


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



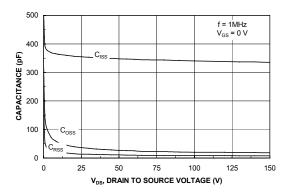


Figure 7. Gate Charge Characteristics.

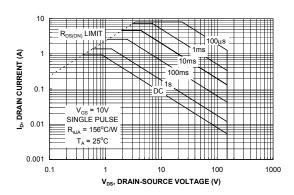


Figure 8. Capacitance Characteristics.

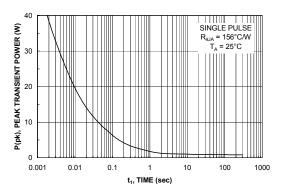


Figure 9. Maximum Safe Operating Area.



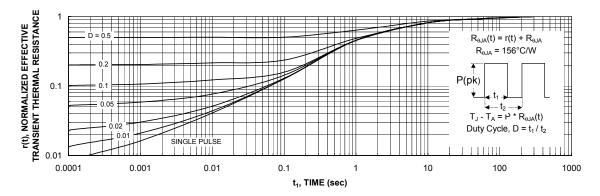


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.



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